Frequency-dependent conductivity of granular metals

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We explore the frequency-dependent conductivity, σ , of granular metals (GMs). Granular metal comprise nanoscale metal islands embedded in a dielectric matrix. We target the metal volume fraction, φ , so that the few-nm diameter metal islands are separated by a ~1 nm dielectric barrier. These metal/insulator composites can be modelled as a complex resistor-capacitor network with complementary tunneling and capacitive conduction paths [1]. At low frequencies, ideal GMs are highly insulating with thermally-assisted tunneling between islands occurring at high E-fields. At high frequencies, capacitive transport dominates; conductivity increases orders of magnitude.

We compare M-SiN_x and M-YSZ (M = Mo or Co; YSZ = yttria-stabilized-zirconia) GM thin films grown via rf co-sputtering on sapphire. Frequency-dependent conductivity is evaluated using impedance spectroscopy at ambient and cryogenic temperatures. Temperature and field-dependent DC conductivity provide insight into tunneling mechanisms. Granular metal structure (Fig. 1a, b) and composition are determined by scanning transmission electron microscopy (STEM) and x-ray photoemission spectroscopy (XPS).

Through careful selection of the metal-insulator system and synthesis optimization, we prepared GM films having $\sigma_{MHz}/\sigma_{DC} > 10^5$ (Fig. 1c). This σ_{MHz}/σ_{DC} ratio was achieved for Mo-SiN_x using depositions conditions that significantly reduced the vacancies present in the sputtered insulator. Analysis of metal/insulator interfaces via XPS showed metal-oxide

formation in M-YSZ and metal-silicide formation in M-SiN_x [2]. Control of deposition conditions can minimize these defects, allowing σ_{MHz}/σ_{DC} optimization for high-pass filters.

This work was supported by the Laboratory Directed Research and Development program at Sandia National Laboratories (SNL). SNL is managed and operated by NTESS under DOE NNSA contract DE-NA0003525. SAND2022-12964 A.

- [1] H. Bakkali *et al.* Sci Rep **6**, 29676 (2016)
- [2] S. Gilbert et al. J. Phys.: Condens. Matter 34 204007 (2022)

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Figure 1: STEM of (a) Co-SiN_x and (b) Mo-SiN_x. In (c), complex impedance of Mo-SiN_x.



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Dr. Laura Biedermann Principal Member of the Technical Staff Electronic, Optical, and Nano Materials Department Sandia National Laboratories

Date: September 23, 2022

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Hi Heather,

Thank you very much for your prompt reply and advice. I will submit the abstract and send Yvonne an e-mail letting her know that I cannot accept the copyright.

Thank you very much for your help!

Laura

From: Heather Korff <Heather@avs.org>

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